

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	37	jang near wen-yueh.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	1039	438/197.cc1s.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	411	(mask\$3 near islands)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	105	(mask\$3 near islands) near15 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	10441	(islands) near15 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	226	(islands) near15 (substrate) near25 (oxidiz\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	105	(islands) near15 (substrate) near25 (oxidiz\$3) near15 (oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	1421	(islands) near15 (substrate) near25 (oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	25	(islands) near15 (substrate) near25 (remov\$3 near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	7	(islands) near15 (wafer) near25 (remov\$3 near oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	17	(islands) near15 (wafer) near25 (remov\$3 near3 oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	73	(islands) near15 (substrate) near25 (remov\$3 near3 oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	1709	(mask\$3) near15 (substrate) near25 (remov\$3 near3 oxide)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	950	(mask\$3) near15 (substrate) near25 (remov\$3 near3 oxide) near15 (etch\$3 or pattern\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	765	(mask\$3) near15 (substrate) near25 (remov\$3 near3 oxide) near15 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	157	(mask\$3) near15 (wafer) near25 (remov\$3 near3 oxide) near15 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 6130380 A	Solar cell and fabrication method thereof
2			US 5627427 A	Silicon tip field emission cathodes
3			US 5199917 A	Silicon tip field emission cathode arrays and fabrication thereof
4			US 5189508 A	Silicon wafer excelling in gettering ability and method for production thereof
5			US 5189505 A	Flexible attachment flip-chip assembly
6			US 5077598 A	Strain relief flip-chip integrated circuit assembly with test fixturing
7			WO 9401875 A	Sub-micron resistor structure for integrated circuit - has isolated released beam carried on single crystal silicon wafer, produced by etching region to define resistive island, oxidising and removing oxide